Supporting Information:

Structural and Electronic Decoupling of C_{60} from Epitaxial Graphene on SiC

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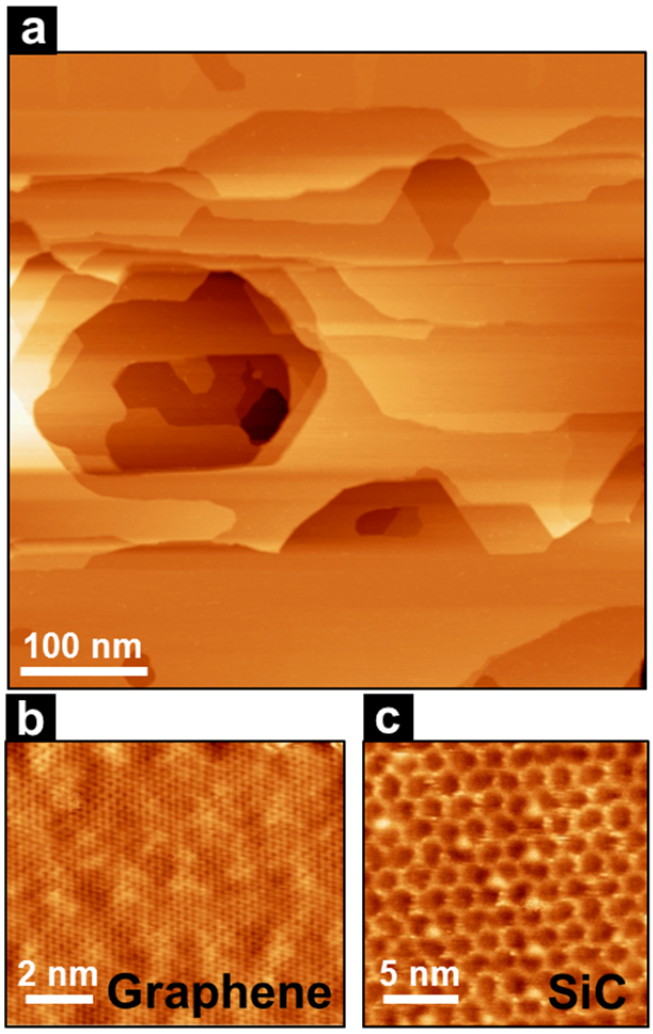

Figure S1: Sample characterization prior to C_{60} deposition: (a) a representative large-scale STM image of a sample (I=100 pA, V=−2 V), (b) STM image of a single-layer of graphene exhibiting honeycomb graphene lattice (I=500 pA, V=−0.1 V), (c) STM image of a $6\sqrt{3} \times 6\sqrt{3}$ R30° reconstructed SiC surface (I=20 pA, V=−1.7 V).

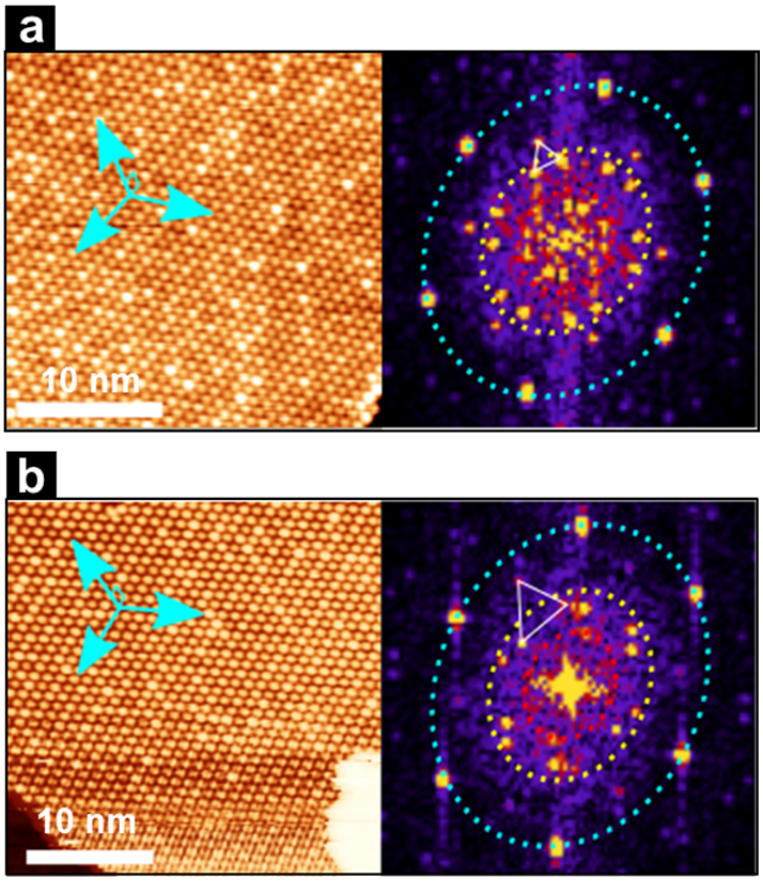

Figure S2: Two additional C_{60} domains on graphene/SiC and associated FFTs showing the continued evolution of superlattice peaks with domain azimuthal angle. Dotted rings corresponding to the C_{60} nearest neighbor distance (cyan) and the 6x6 (yellow) and $6\sqrt{3} \times 6\sqrt{3}$ (red) unit cell parameters are indicated on each FFT. Note that there are no obvious peaks located on the $6\sqrt{3} \times 6\sqrt{3}$ ring. Peaks arise from the primary close-packed C_{60} lattice and the superlattice (indicated with a small triangle).

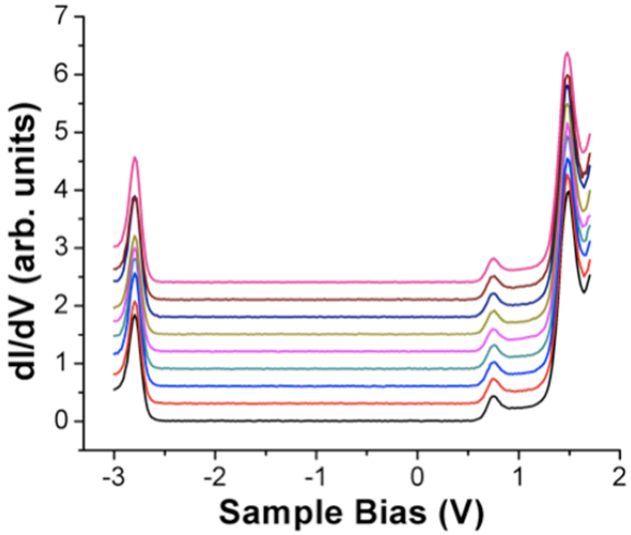

Figure S3: Differential conductance dI/dV spectra measured at 45 K for C_{60} molecules adsorbed onto monolayer graphene on SiC. Each dI/dV curve was averaged over 20 individual spectra including forward and backward sweeps. Tunneling parameters were I=1.5 nA and V=1.7 V.